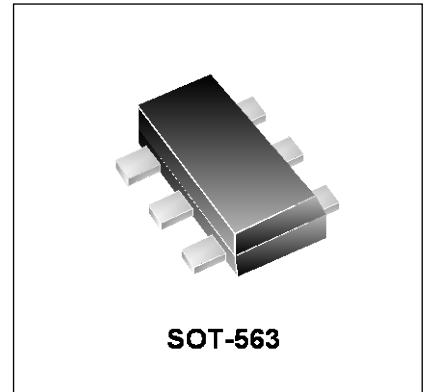


Features

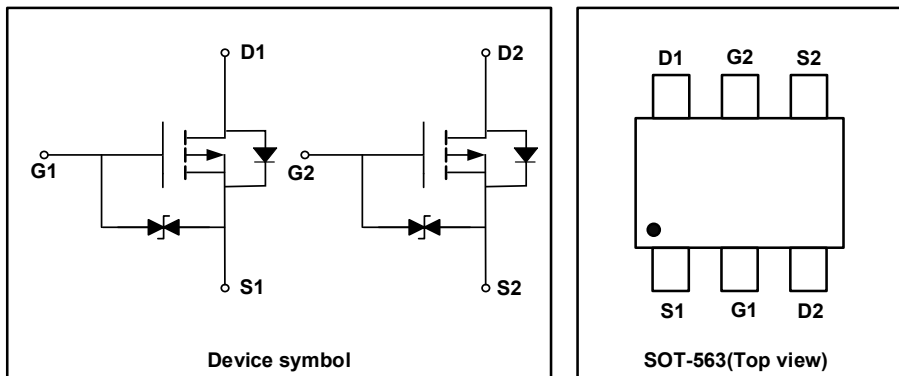
- Way-on Small Signal MOSFETs
- $V_{DS} = -20V$, $I_D = -0.66A$
 $R_{DS(on)} < 0.52\Omega @ V_{GS} = -4.5 V$
 $R_{DS(on)} < 0.78\Omega @ V_{GS} = -2.5 V$
- Trench LV MOSFET Technology
- ESD Protected

Mechanical Characteristics

- SOT-563 Package
- Marking : Making Code
- RoHS Compliant



Schematic & PIN Configuration



Absolute Maximum Rating ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-0.66	A
Pulsed Drain Current ¹	I_{DM}	-2.64	A
Power Dissipation	P_D	150	mW
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient ²	$R_{\theta JA}$	833	$^\circ C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-20	-	-	V
Gate-body Leakage Current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±10V	-	-	±20	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20V, V _{GS} = 0V	-	-	-1	μA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.3	-0.65	-1.1	V
Drain-Source On-state Resistance ³	R _{DS(on)}	V _{GS} = -4.5V, I _D = -0.66A	-	0.45	0.52	Ω
		V _{GS} = -2.5V, I _D = -0.6A	-	0.65	0.78	
		V _{GS} = -1.8V, I _D = -0.5A	-	0.95	-	
Dynamic Characteristics⁴						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = -10V, f = 1MHz	-	77	-	pF
Output Capacitance	C _{oss}		-	13	-	
Reverse Transfer Capacitance	C _{rss}		-	10.5	-	
Switching Characteristics⁴						
Turn-On Delay Time	t _{d(on)}	V _{GS} = -4.5V, V _{DD} = -10V, I _D = -0.66A, R _G =3Ω	-	9	-	ns
Turn-On Rise Time	t _r		-	5.7	-	
Turn-Off Delay Time	t _{d(off)}		-	32.6	-	
Turn- Off Fall Time	t _f		-	20.3	-	
Source-Drain Diode Characteristics						
Diode Forward Voltage ³	V _{SD}	I _S = -0.5A, V _{GS} = 0V	-	-	-1.2	V
Continuous Source Current	I _S		-	-	-0.66	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C.
2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width≤300μs, duty cycle≤2%.
4. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

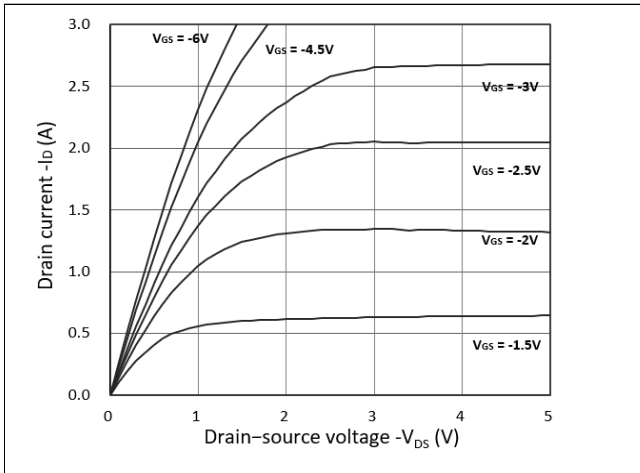


Figure 1. Output Characteristics

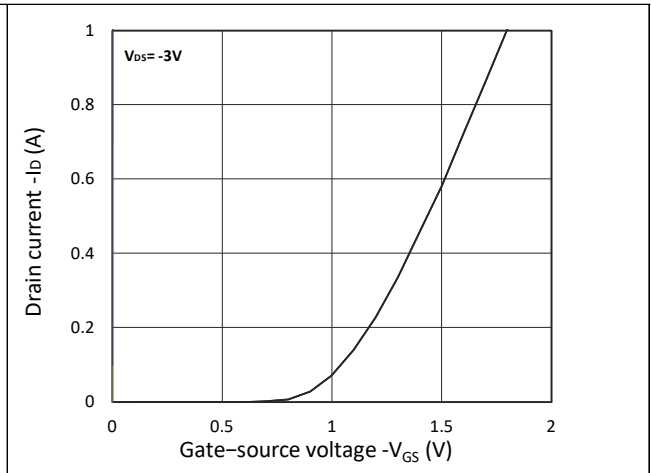


Figure 2. Transfer Characteristics

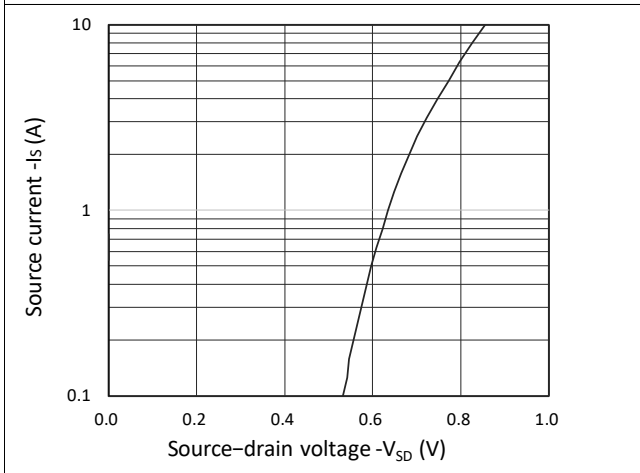


Figure 3. Forward Characteristics of Reverse

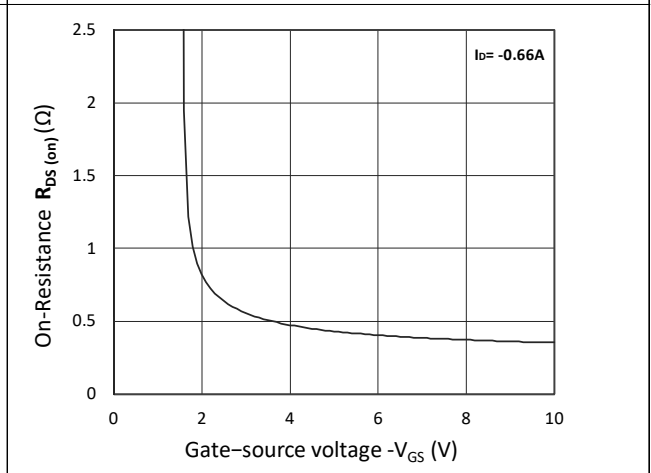


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

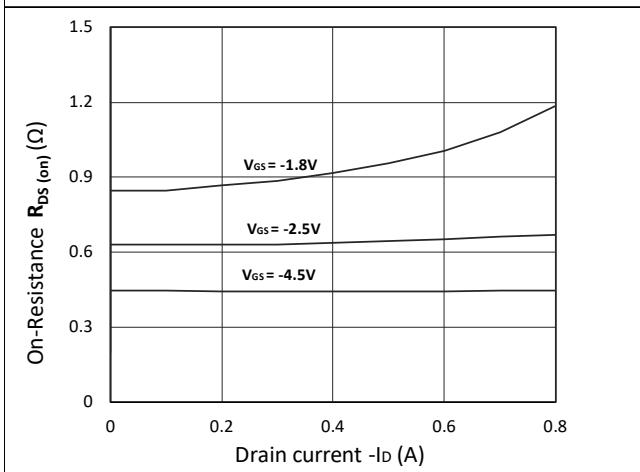


Figure 5. $R_{DS(ON)}$ vs. I_D

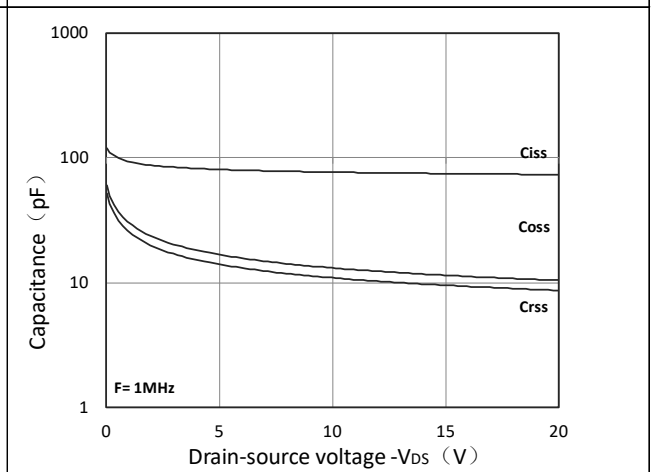


Figure 6. Capacitance Characteristics

Outline Drawing – SOT-563

PACKAGE OUTLINE

SOT-563

DIMENSIONS				
SYMBOL	MILLIMETER		INCHES	
	MIN	MIN	MIN	MAX
A	0.52	0.60	0.020	0.024
A1	0.00	0.05	0.000	0.002
e	0.45	0.55	0.018	0.022
c	0.09	0.16	0.004	0.006
D	1.50	1.70	0.059	0.067
b	0.17	0.27	0.007	0.011
E1	1.10	1.30	0.043	0.051
E	1.50	1.70	0.059	0.067
L	0.10	0.30	0.004	0.012
θ	7°REF		7°REF	

DIMENSIONS		
DIM	INCHES	MILLIMETERS
Z	0.075	1.91
G	0.0350	0.89
P	0.020TYP	0.51 TYP
X	0.012	0.30
Y	0.020	0.51

Notes

1. Dimensioning and tolerances per ANSI Y14.5M, 1985.
2. Controlling Dimension: Inches
3. Dimensions are exclusive of mold flash and metal burrs.

Marking Codes

Part Number	WM02DP06T
Marking Code	

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

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For additional information, please contact your local Sales Representative.

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Specifications are subject to change without notice.
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.
Users should verify actual device performance in their specific applications.